

IN THE CLAIMS:

Please amend claims 1, 9, 10, and 11 in "clean" format, as follows:

1. (Amended) An electroluminescence device, comprising:

*Sub B<sup>2</sup>*  
~~an electroluminescence element having a light emissive layer provided between first and second electrodes;~~

*A*  
~~a first thin film transistor receiving a selection signal at its gate to acquire a data signal; and~~

~~a second thin film transistor provided between a driving power supply and said electroluminescence element, and controlling power supplied from said driving power supply to said electroluminescence element in accordance with the data signal supplied from said first thin film transistor; wherein~~

~~said first thin film transistor is a double gate type having a lightly doped drain structure, said first thin film transistor has an n-channel, an offset structure, and a multigate structure; and~~

~~said second thin film transistor has a p-channel.~~

*Sub B<sup>2</sup>*  
9. (Amended) An electroluminescence display device, comprising:

*A<sup>2</sup>*  
~~an electroluminescence element having a light emissive layer provided between an anode and a cathode;~~

~~a first thin film transistor having an active layer which is formed of a non-single crystalline semiconductor film and which includes a source connected to a storage capacitor, a drain connected to a drain signal line, and a gate electrode provided over a channel of said active layer and connected to a gate signal line; and~~

*A<sup>2</sup>*  
~~a second thin film transistor having an active layer which is formed of a non-single crystalline semiconductor film and which includes a drain connected to a driving power supply of said electroluminescence element, and a gate electrode connected to the source of said first thin film transistor; wherein~~

~~said first thin film transistor is a double gate type having a lightly doped drain structure, said first thin film transistor has an n-channel, an offset structure, and a multigate structure; and~~

~~said second thin film transistor has a p-channel.~~

*Sub B3*

10. (Amended) An electroluminescence display device, comprising:  
an electroluminescence element having a light emissive layer provided between an  
anode and a cathode;  
a first thin film transistor having an active layer which is formed of a non-single  
crystalline semiconductor film and which includes a source connected to a storage capacitor,  
a drain connected to a drain signal line, and a gate electrode provided under a channel of said  
active layer and connected to a gate signal line; and

a second thin film transistor having an active layer which is formed of a non-single  
crystalline semiconductor film and which includes a drain connected to a driving power  
supply of said electroluminescence element, and a gate electrode connected to the source of  
said first thin film transistor; wherein

*Control A2*

said first thin film transistor is a double gate type having a lightly doped drain  
structure, said first thin film transistor has an n-channel, an offset structure, and a multigate  
structure; and

said second thin film transistor has a p-channel.

11. (Amended) A light emissive device, comprising:  
a light emissive element having a light emissive layer provided between first and  
second electrodes;

a first thin film transistor receiving a selection signal at its gate to acquire a data  
signal; and

a second thin film transistor provided between a driving power supply and said  
element, and controlling power supplied from said driving power supply to said element in  
accordance with the data signal supplied from said first thin film transistor; wherein

said first thin film transistor is a double gate type having a lightly doped drain  
structure, said first thin film transistor has an n-channel, an offset structure, and a multigate  
structure; and

said second thin film transistor has a p-channel.